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				ATMI-272-CIP		09/874,102	
INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)		APPLICANT Peter C. Van Buskirk, et al.		FILING DATE		GROUP	
				June 5, 2001		1762 1263	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AA	68/975,366 5,976,928	11/1999	Van Buskirk and Kirlin				11/20/98
AB	6,018,065	1/2/00	Baum, et al.				
AC	5,911,887	6/15/99	Smith, et al.				
AD	5,814,238	9/29/98	Ashby, et al.				
AE	4,659,426	4/21/87	Fuller, et al.				
FOREIGN PATENT DOCUMENTS							
	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	NO
TECHNOLOGY CENTER 1700							
OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)							
AF	Koteki, D.E., "A Review of High Dielectric Materials for DRAM Capacitors", <i>Integ. Ferro.</i> , 1997, Vol. 16, pp. 1-19.						
AG	Jeon, et al., "Thermal Stability of Ir/Polycrystalline-Si Structure for Bottom Electrode of Integrated Ferroelectric Capacitors", <i>Appl. Physics Lett.</i> , 1997, Vol. 71(4), pp. 467-469.						
AH	Williams, et al., "Etch Rates for Micromachining Processing", <i>Journ. For Microelectromechanical Systems</i> , December 1996, Vol. 5 (4), pp. 256-269						
AI	Vugts, et al., "Si/XeF ₂ Etching-Temperature Dependence", 1996, <i>J. Vac. Sci. Tech. A</i> , Vol. 14(5), pp. 2766-2774						
AJ	P.C. Fazan, et al., "Stacked Capacitor Modules for 64 Mb DRAMs and Beyond", <i>Semiconductor Inter.</i> , 1992, Vol. 108, pp. 108-112						
AK	L. H. Parker, et al., Ferroelectric Materials for 64Mb and 256Mb DRAMs", <i>IEEE Circuits and Devices Mag.</i> , Jan. 1990, pp. 17-26						
Continue on Page 2							
EXAMINER					DATE CONSIDERED		
[Signature]					12/1/03		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.							

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BA	R. E. Sievers, et al., "Volatile Barium B-Diketonates for Use as MOCVD Precursors", <i>Coord. Chem. Rev.</i> , 1993, pp. 285-291.
BB	C. Farrell, et al., "A Reactive Ion Etch Study for Producing Patterned Platinum Structures", Presented at ISIF 96, March 18,19,20, 1996 Tempe AZ. (to be published in <i>Integrated Ferroelectrics</i>).
BC	K. R. Milkove and C. X. Wang, "Insight into the dry cleaning of Fence Patterned Platinum Structures", <i>J. Vac. Sci. Tech. A</i> , 1997, Vol. 15(3), pp. 596-603
BD	Chang, F.I., et al., "Gas Phase Silicon Micromachining with Xenon Difluoride", <i>Proc of SPIE</i> , 1995, Vol. 2641, pp. 117-128.
BE	Bensaola, A. et al., "Low Temperature Ion Beam Enhanced Etching of Tungsten Films with Xenon Difluoride", <i>Appl. Phys. Lett.</i> , Dec. 1986, Vol. 49(24), pp. 1663-1664
BF	G. Stauff, "BaSrTiO3 Etching for Advanced Microelectronic Devices, U.S. Army Missile Command, Report Number, DAAH01-96-C-R035, 1/10/96-1/30/98.

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EXAMINER <i>Alan E. Olson</i>	DATE CONSIDERED 12/1/03
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